Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- · Logic-level compatible
- · Very fast switching
- · Enhanced power dissipation capability of 1.4 W
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- · High-speed line driver
- · High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-4.4	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -3.3 A; T_j = 25 °C		-	60	80	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D
2	D	drain		
3	G	gate		G \downarrow \downarrow \downarrow
4	S	source	TSOP6 (SOT457)	
5	D	drain		
6	D	drain		S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
PMN70EPE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457				

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN70EPE	G2

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-4.4	Α
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-3.3	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-2.1	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-14	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	570	mW
			[1]	-	1.4	W
		T _{sp} = 25 °C		-	6.25	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.4	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

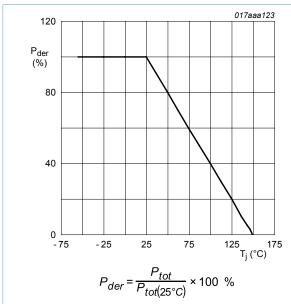


Fig. 1. Normalized total power dissipation as a function of junction temperature

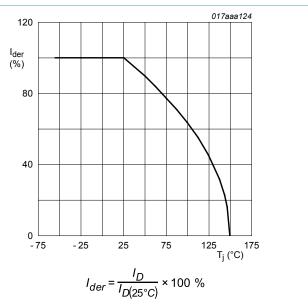
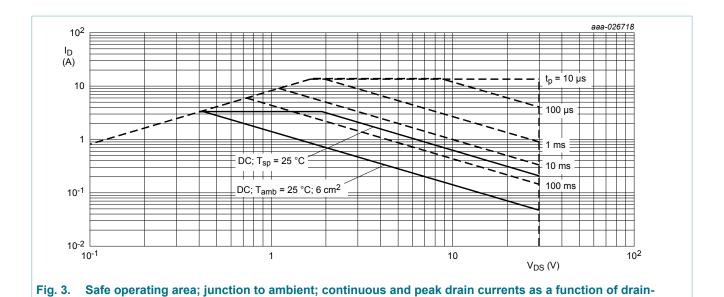


Fig. 2. Normalized continuous drain current as a function of junction temperature

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source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	190	220	K/W
	from junction to ambient		[2]	-	78	90	K/W
		in free air; t ≤ 5 s	[2]	-	47	54	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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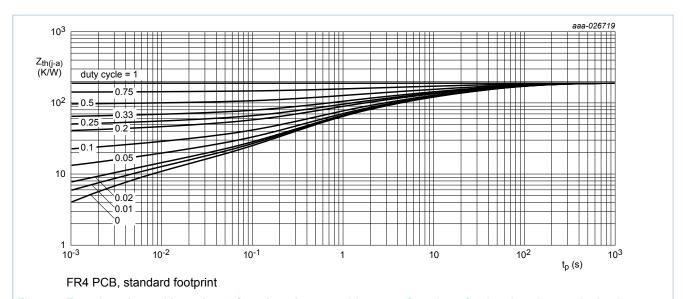


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

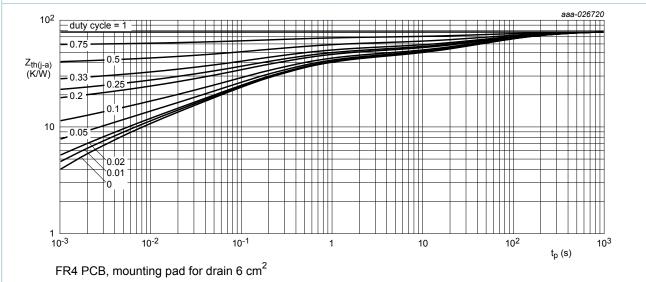


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
racteristics					
drain-source breakdown voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-30	-	-	V
gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1	-2	-3	V
drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-1	μΑ
gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μΑ
	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μΑ
	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
	V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μΑ
	V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
	V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
drain-source on-state	V_{GS} = -10 V; I_D = -3.3 A; T_j = 25 °C	-	60	80	mΩ
resistance	V_{GS} = -10 V; I_D = -3.3 A; T_j = 150 °C	-	91	121	mΩ
	V_{GS} = -4.5 V; I_{D} = -2.6 A; T_{j} = 25 °C	-	96	140	mΩ
forward transconductance	V_{DS} = -10 V; I_{D} = -2 A; T_{j} = 25 °C	-	12.6	-	S
gate resistance	f = 1 MHz; T _j = 25 °C	-	12	-	Ω
haracteristics					
total gate charge	$V_{DS} = -15 \text{ V}; I_D = -3.3 \text{ A}; V_{GS} = -10 \text{ V};$	-	6.5	11.5	nC
gate-source charge	T _j = 25 °C	-	1.2	-	nC
gate-drain charge		-	1.2	-	nC
input capacitance	$V_{DS} = -15 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	370	-	pF
output capacitance	T _j = 25 °C	-	64	-	pF
reverse transfer capacitance		-	44	-	pF
turn-on delay time	V_{DS} = -15 V; I_{D} = -3.3 A; V_{GS} = -10 V;	-	5	-	ns
rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	8	-	ns
turn-off delay time		-	19	-	ns
fall time		-	7.5	-	ns
ain diode		'	,		,
source-drain voltage	$I_S = -1.4 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$	_	-0.8	-1.2	V
	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current drain-source on-state resistance forward transconductance gate resistance total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time ain diode	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current Grain leakage current gate leakage current Grain leakage Grain leakage current Grain leakage ou V; T _j = 25 °C Grain leakage ou V; T _j = 25 °C Grain leakage ou V; T _j = 25 °C Grain leakage ou V; T _j = 25 °C	acteristics drain-source breakdown voltage ID = -250 μA; VGS = 0 V; TJ = 25 °C -30 gate-source threshold voltage ID = -250 μA; VDS = VGS; TJ = 25 °C -1 drain leakage current VDS = -30 V; VGS = 0 V; TJ = 25 °C - gate leakage current VGS = 20 V; VDS = 0 V; TJ = 25 °C - VGS = -20 V; VDS = 0 V; TJ = 25 °C - VGS = -10 V; VDS = 0 V; TJ = 25 °C - VGS = -10 V; VDS = 0 V; TJ = 25 °C - VGS = -4.5 V; VDS = 0 V; TJ = 25 °C - VGS = -4.5 V; VDS = 0 V; TJ = 25 °C - VGS = -10 V; ID = -3.3 A; TJ = 150 °C - VGS = -10 V; ID = -3.3 A; TJ = 25 °C - VGS = -10 V; ID = -2.6 A; TJ = 25 °C - forward transconductance TJ = -25 °C gate resistance F = 1 MHz; TJ = 25 °C haracteristics - total gate charge VDS = -15 V; ID = -3.3 A; VGS = -10 V; TJ = 25 °C gate-source charge - gate-drain charge - input capacitance VDS = -15 V; ID = -3.3 A; VGS = -10 V; TJ = 25 °C - - <td< td=""><td> drain-source Drawford ID = -250 μA; VGS = 0 V; Tj = 25 °C Square S</td><td>acteristics drain-source breakdown voltage $I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ -30 - - gate-source threshold voltage $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ -1 -2 -3 drain leakage current $V_{DS} = -30 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -10 gate leakage current $V_{GS} = 20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -10 $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -10 $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -10 $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -10 $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -100 drain-source on-state resistance $V_{GS} = -10 \ V; \ I_D = -3.3 \ A; \ T_j = 25 \ ^{\circ}C$ - - -100 $V_{GS} = -10 \ V; \ I_D = -3.3 \ A; \ T_j = 25 \ ^{\circ}C$ - - - -100 drain-source on-state resistance $V_{GS} = -10 \ V; \ I_D = -2.6 \ A; \ T_j = 25 \ ^{\circ}C$ - - - - <t< td=""></t<></td></td<>	drain-source Drawford ID = -250 μA; VGS = 0 V; Tj = 25 °C Square S	acteristics drain-source breakdown voltage $I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ -30 - - gate-source threshold voltage $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ -1 -2 -3 drain leakage current $V_{DS} = -30 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -10 gate leakage current $V_{GS} = 20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -10 $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -10 $V_{GS} = 10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -10 $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -10 $V_{GS} = -10 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ - - -100 drain-source on-state resistance $V_{GS} = -10 \ V; \ I_D = -3.3 \ A; \ T_j = 25 \ ^{\circ}C$ - - -100 $V_{GS} = -10 \ V; \ I_D = -3.3 \ A; \ T_j = 25 \ ^{\circ}C$ - - - -100 drain-source on-state resistance $V_{GS} = -10 \ V; \ I_D = -2.6 \ A; \ T_j = 25 \ ^{\circ}C$ - - - - <t< td=""></t<>

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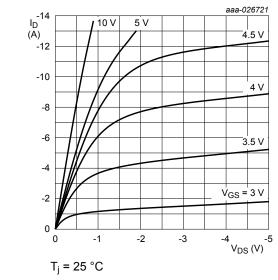


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

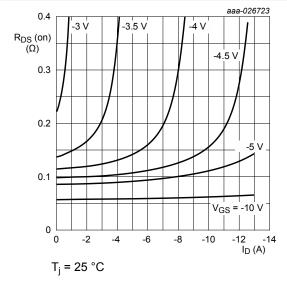


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

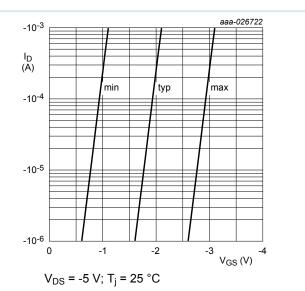


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

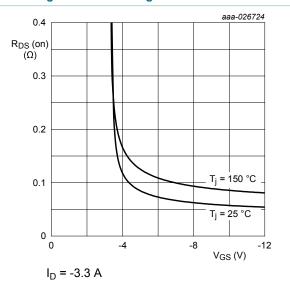


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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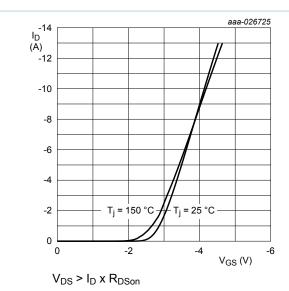


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

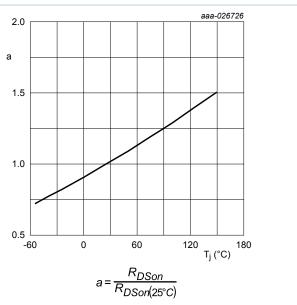


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

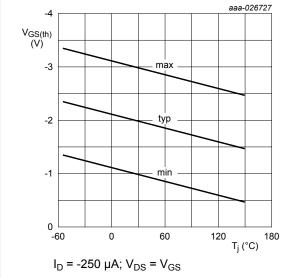


Fig. 12. Gate-source threshold voltage as a function of junction temperature

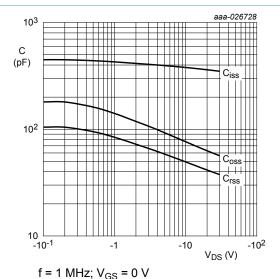


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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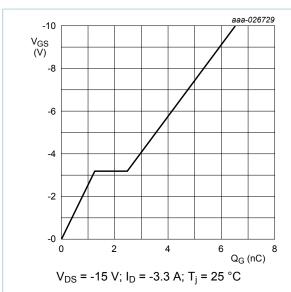


Fig. 14. Gate-source voltage as a function of gate charge; typical values

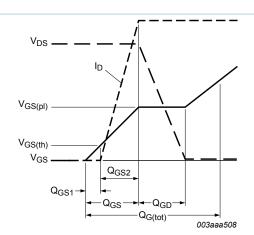


Fig. 15. Gate charge waveform definitions

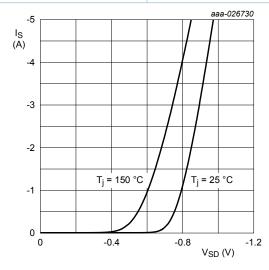
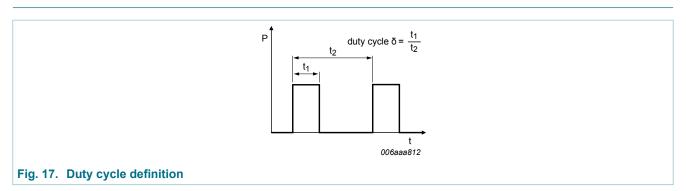


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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12. Package outline

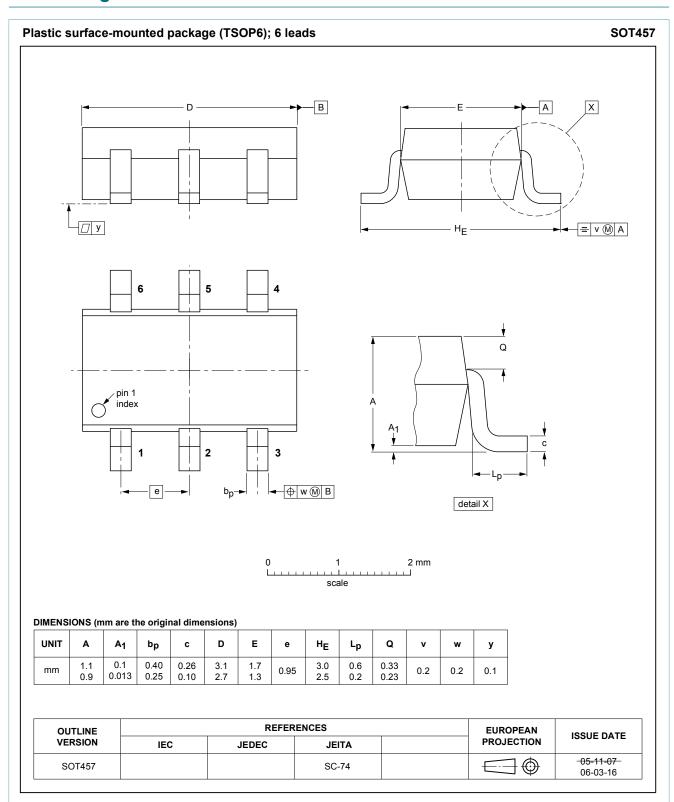
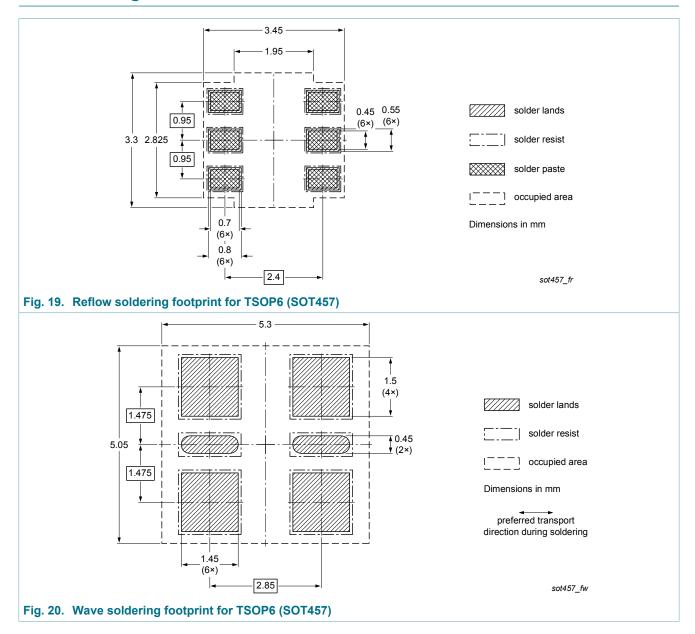


Fig. 18. Package outline TSOP6 (SOT457)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN70EPE v.1	20170523	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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